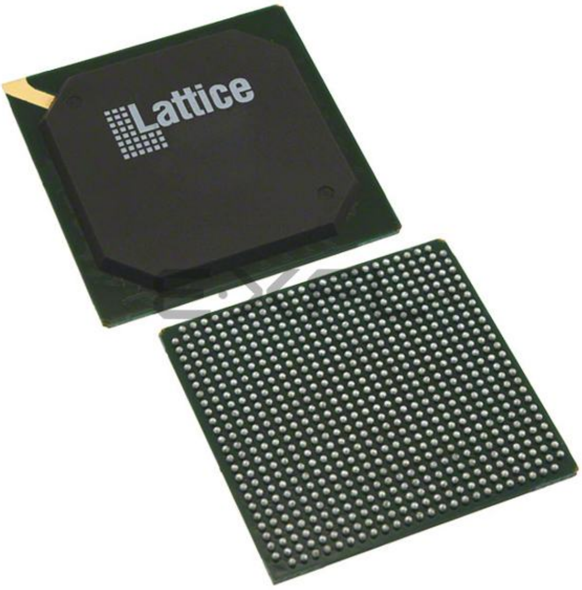

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-7fn672c

PLL/DLL Cascading

LatticeECP3 devices have been designed to allow certain combinations of PLL and DLL cascading. The allowable combinations are:

- PLL to PLL supported
- PLL to DLL supported

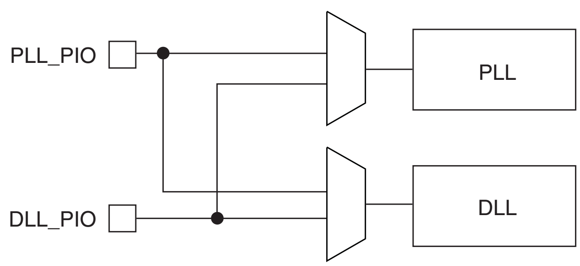
The DLLs in the LatticeECP3 are used to shift the clock in relation to the data for source synchronous inputs. PLLs are used for frequency synthesis and clock generation for source synchronous interfaces. Cascading PLL and DLL blocks allows applications to utilize the unique benefits of both DLLs and PLLs.

For further information about the DLL, please see the list of technical documentation at the end of this data sheet.

PLL/DLL PIO Input Pin Connections

All LatticeECP3 devices contains two DLLs and up to ten PLLs, arranged in quadrants. If a PLL and a DLL are next to each other, they share input pins as shown in the Figure 2-7.

Figure 2-7. Sharing of PIO Pins by PLLs and DLLs in LatticeECP3 Devices



Note: Not every PLL has an associated DLL.

Clock Dividers

LatticeECP3 devices have two clock dividers, one on the left side and one on the right side of the device. These are intended to generate a slower-speed system clock from a high-speed edge clock. The block operates in a ÷2, ÷4 or ÷8 mode and maintains a known phase relationship between the divided down clock and the high-speed clock based on the release of its reset signal. The clock dividers can be fed from selected PLL/DLL outputs, the Slave Delay lines, routing or from an external clock input. The clock divider outputs serve as primary clock sources and feed into the clock distribution network. The Reset (RST) control signal resets input and asynchronously forces all outputs to low. The RELEASE signal releases outputs synchronously to the input clock. For further information on clock dividers, please see TN1178, LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide. Figure 2-8 shows the clock divider connections.

Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

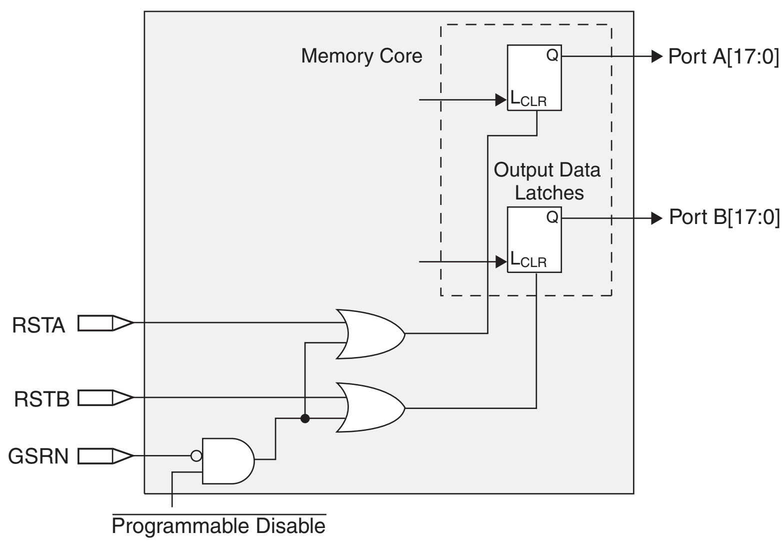
EBR memory supports the following forms of write behavior for single port or dual port operation:

1. **Normal** – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
2. **Write Through** – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.
3. **Read-Before-Write (EA devices only)** – When new data is written, the old content of the address appears at the output. This mode is supported for x9, x18, and x36 data widths.

Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B, respectively. The Global Reset (GSRN) signal can reset both ports. The output data latches and associated resets for both ports are as shown in Figure 2-22.

Figure 2-22. Memory Core Reset



For further information on the sysMEM EBR block, please see the list of technical documentation at the end of this data sheet.

sysDSP™ Slice

The LatticeECP3 family provides an enhanced sysDSP architecture, making it ideally suited for low-cost, high-performance Digital Signal Processing (DSP) applications. Typical functions used in these applications are Finite Impulse Response (FIR) filters, Fast Fourier Transforms (FFT) functions, Correlators, Reed-Solomon/Turbo/Convolution encoders and decoders. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

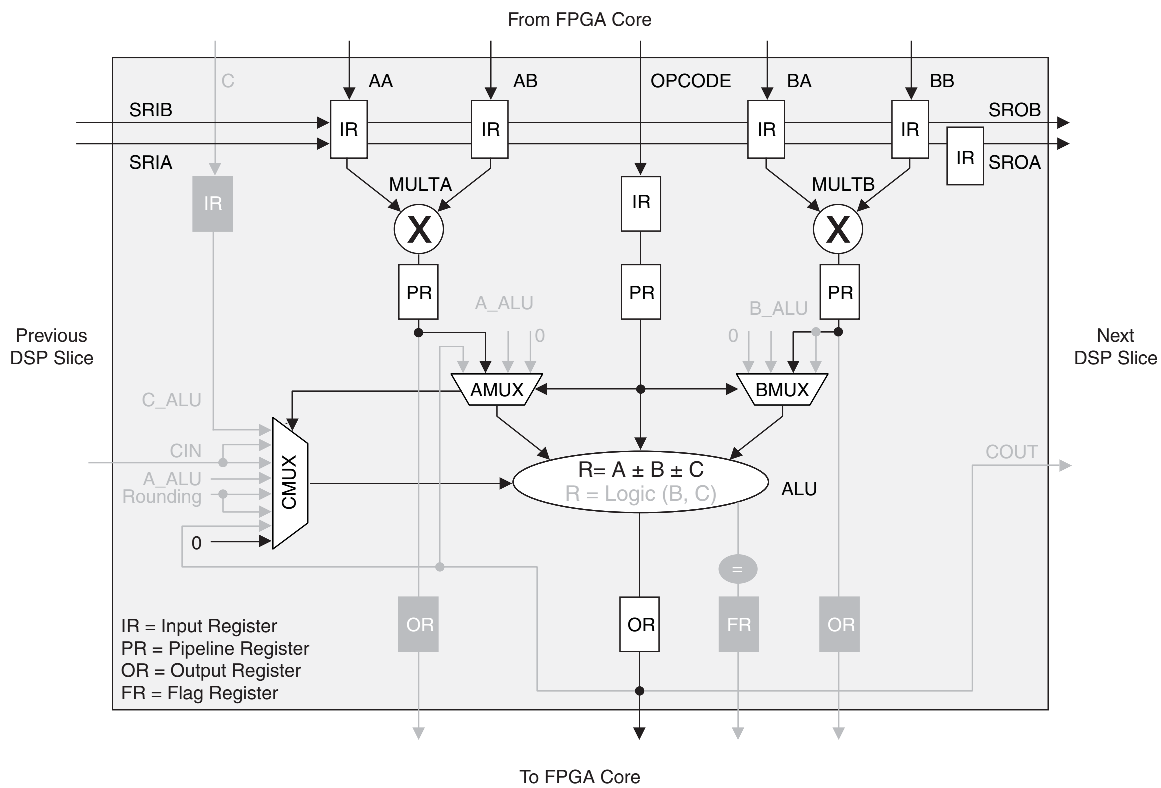
sysDSP Slice Approach Compared to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. The LatticeECP3, on the other hand, has many DSP slices that support different data widths.

MULTADDSUB DSP Element

In this case, the operands AA and AB are multiplied and the result is added/subtracted with the result of the multiplier operation of operands BA and BB. The user can enable the input, output and pipeline registers. Figure 2-29 shows the MULTADDSUB sysDSP element.

Figure 2-29. MULTADDSUB



DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces, a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The delay required for the DQS signal is generated by two dedicated DLLs (DDR DLL) on opposite side of the device. Each DLL creates DQS delays in its half of the device as shown in Figure 2-36. The DDR DLL on the left side will generate delays for all the DQS Strobe pins on Banks 0, 7 and 6 and DDR DLL on the right will generate delays for all the DQS pins on Banks 1, 2 and 3. The DDR DLL loop compensates for temperature, voltage and process variations by using the system clock and DLL feedback loop. DDR DLL communicates the required delay to the DQS delay block using a 7-bit calibration bus (DCNTL[6:0])

The DQS signal (selected PIOs only, as shown in Figure 2-35) feeds from the PAD through a DQS control logic block to a dedicated DQS routing resource. The DQS control logic block consists of DQS Read Control logic block that generates control signals for the read side and DQS Write Control logic that generates the control signals required for the write side. A more detailed DQS control diagram is shown in Figure 2-37, which shows how the DQS control blocks interact with the data paths.

The DQS Read control logic receives the delay generated by the DDR DLL on its side and delays the incoming DQS signal by 90 degrees. This delayed ECLKDQSR is routed to 10 or 11 DQ pads covered by that DQS signal. This block also contains a polarity control logic that generates a DDRCLKPOL signal, which controls the polarity of the clock to the sync registers in the input register blocks. The DQS Read control logic also generates a DDRLAT signal that is in the input register block to transfer data from the first set of DDR register to the second set of DDR registers when using the DDRX2 gearbox mode for DDR3 memory interface.

The DQS Write control logic block generates the DQCLK0 and DQCLK1 clocks used to control the output gearing in the Output register block which generates the DDR data output and the DQS output. They are also used to control the generation of the DQS output through the DQS output register block. In addition to the DCNTL [6:0] input from the DDR DLL, the DQS Write control block also uses a Dynamic Delay DYN DEL [7:0] attribute which is used to further delay the DQS to accomplish the write leveling found in DDR3 memory. Write leveling is controlled by the DDR memory controller implementation. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock. This will generate the DQSW signal used to generate the DQS output in the DQS output register block.

Figure 2-36 and Figure 2-37 show how the DQS transition signals that are routed to the PIOs.

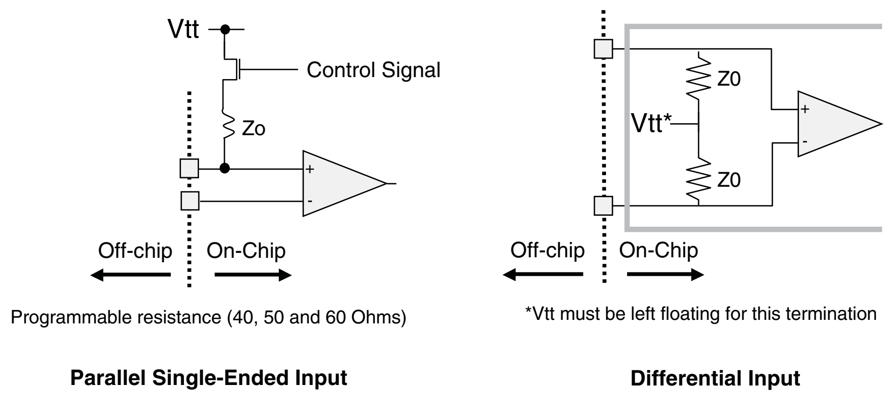
Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

On-Chip Programmable Termination

The LatticeECP3 supports a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 40, 50, or 60 Ohms. External termination to Vtt should be used for DDR2 and DDR3 memory controller implementation.
- Common mode termination of 80, 100, 120 Ohms for differential inputs

Figure 2-39. On-Chip Termination



See Table 2-12 for termination options for input modes.

Table 2-12. On-Chip Termination Options for Input Modes

IO_TYPE	TERMINATE to VTT[1, 2]	DIFFERENTIAL TERMINATION RESISTOR[1]
LVDS25	þ	80, 100, 120
BLVDS25	þ	80, 100, 120
MLVDS	þ	80, 100, 120
HSTL18_I	40, 50, 60	þ
HSTL18_II	40, 50, 60	þ
HSTL18D_I	40, 50, 60	þ
HSTL18D_II	40, 50, 60	þ
HSTL15_I	40, 50, 60	þ
HSTL15D_I	40, 50, 60	þ
SSTL25_I	40, 50, 60	þ
SSTL25_II	40, 50, 60	þ
SSTL25D_I	40, 50, 60	þ
SSTL25D_II	40, 50, 60	þ
SSTL18_I	40, 50, 60	þ
SSTL18_II	40, 50, 60	þ
SSTL18D_I	40, 50, 60	þ
SSTL18D_II	40, 50, 60	þ
SSTL15	40, 50, 60	þ
SSTL15D	40, 50, 60	þ

1. TERMINATE to VTT and DIFFERENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.
   Use of TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank.
   On-chip termination tolerance +/– 20%
2. External termination to VTT should be used when implementing DDR2 and DDR3 memory controller.

Figure 2-40. SERDES/PCS Quads (LatticeECP3-150)

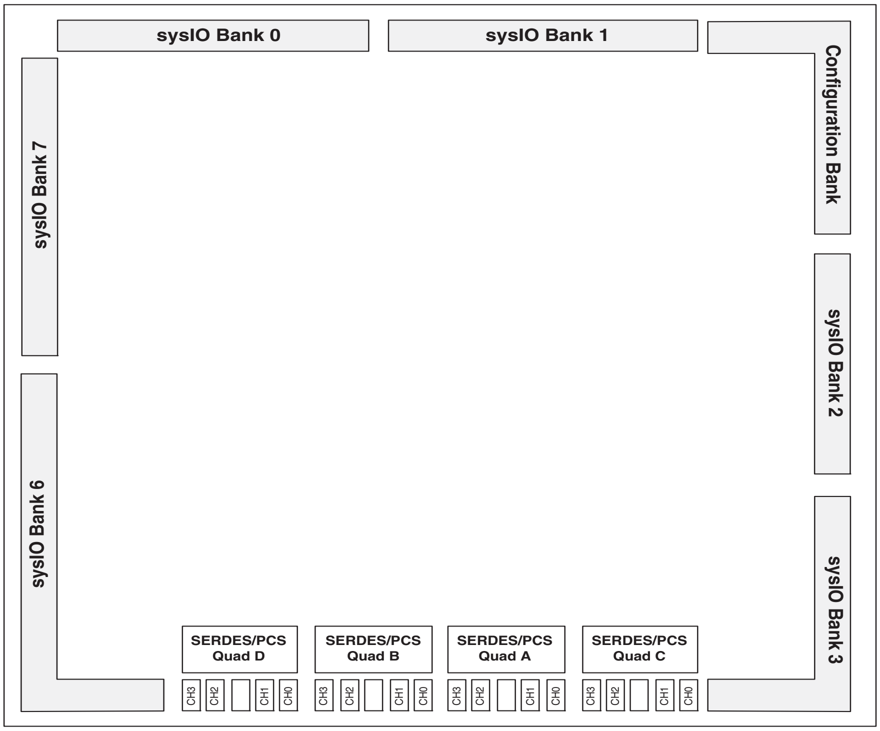


Table 2-13. LatticeECP3 SERDES Standard Support

Standard	Data Rate (Mbps)	Number of General/Link Width	Encoding Style
PCI Express 1.1	2500	x1, x2, x4	8b10b
Gigabit Ethernet	1250, 2500	x1	8b10b
SGMII	1250	x1	8b10b
XAUI	3125	x4	8b10b
Serial RapidIO Type I, Serial RapidIO Type II, Serial RapidIO Type III	1250, 2500, 3125	x1, x4	8b10b
CPRI-1, CPRI-2, CPRI-3, CPRI-4	614.4, 1228.8, 2457.6, 3072.0	x1	8b10b
SD-SDI (259M, 344M)	143[1], 177[1], 270, 360, 540	x1	NRZI/Scrambled
HD-SDI (292M)	1483.5, 1485	x1	NRZI/Scrambled
3G-SDI (424M)	2967, 2970	x1	NRZI/Scrambled
SONET-STS-3[2]	155.52	x1	N/A
SONET-STS-12[2]	622.08	x1	N/A
SONET-STS-48[2]	2488	x1	N/A

1. For slower rates, the SERDES are bypassed and CML signals are directly connected to the FPGA routing.
2. The SONET protocol is supported in 8-bit SERDES mode. See TN1176 Lattice ECP3 SERDES/PCS Usage Guide for more information.

sysI/O Single-Ended DC Electrical Characteristics

Input/Output Standard	V_{IL} Min. (V)	V_{IL} Max. (V)	V_{IH} Min. (V)	V_{IH} Max. (V)	V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
LVCMOS33	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, -8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS25	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS18	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	–16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS15	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	8, 4	–8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS12	–0.3	0.35 V_{CC}	0.65 V_{CC}	3.6	0.4	V_{CCIO} - 0.4	6, 2	–6, –2
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVTTL33	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
PCI33	–0.3	0.3 V_{CCIO}	0.5 V_{CCIO}	3.6	0.1 V_{CCIO}	0.9 V_{CCIO}	1.5	–0.5
SSTL18_I	–0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.4	V_{CCIO} - 0.4	6.7	–6.7
SSTL18_II (DDR2 Memory)	–0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.28	V_{CCIO} - 0.28	8	–8
							11	–11
SSTL2_I	–0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	7.6	–7.6
							12	–12
SSTL2_II (DDR Memory)	–0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.35	V_{CCIO} - 0.43	15.2	–15.2
							20	–20
SSTL3_I	–0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.7	V_{CCIO} - 1.1	8	–8
SSTL3_II	–0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.5	V_{CCIO} - 0.9	16	–16
SSTL15 (DDR3 Memory)	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.3	V_{CCIO} - 0.3	7.5	–7.5
						V_{CCIO} * 0.8	9	–9
HSTL15_I	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
HSTL18_I	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	8	–8
							12	–12
HSTL18_II	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	16	–16

1. For electromigration, the average DC current drawn by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed n * 8 mA, where n is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

Typical Building Block Function Performance

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)[1, 2, 3]

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	4.7	ns
32-bit Decoder	4.7	ns
64-bit Decoder	5.7	ns
4:1 MUX	4.1	ns
8:1 MUX	4.3	ns
16:1 MUX	4.7	ns
32:1 MUX	4.8	ns

1. These functions were generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

Register-to-Register Performance[1, 2, 3]

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	500	MHz
32-bit Decoder	500	MHz
64-bit Decoder	500	MHz
4:1 MUX	500	MHz
8:1 MUX	500	MHz
16:1 MUX	500	MHz
32:1 MUX	445	MHz
8-bit adder	500	MHz
16-bit adder	500	MHz
64-bit adder	305	MHz
16-bit counter	500	MHz
32-bit counter	460	MHz
64-bit counter	320	MHz
64-bit accumulator	315	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	340	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	340	MHz
1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers	130	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	245	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	500	MHz
32x4 Pseudo-Dual Port RAM	500	MHz
64x8 Pseudo-Dual Port RAM	400	MHz
DSP Function		
18x18 Multiplier (All Registers)	400	MHz
9x9 Multiplier (All Registers)	400	MHz
36x36 Multiply (All Registers)	260	MHz

LatticeECP3 External Switching Characteristics [1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Clocks									
Primary Clock[6]									
f_{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-150EA	—	500	—	420	—	375	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-150EA	—	300	—	330	—	360	ps
t_{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-150EA	—	250	—	280	—	300	ps
f_{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t_{W_PRI}	Pulse Width for Primary Clock	ECP3-70EA/95EA	0.8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-70EA/95EA	—	360	—	370	—	380	ps
t_{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-70EA/95EA	—	310	—	320	—	330	ps
f_{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-35EA	—	500	—	420	—	375	MHz
t_{W_PRI}	Pulse Width for Primary Clock	ECP3-35EA	0. 8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-35EA	—	300	—	330	—	360	ps
t_{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-35EA	—	250	—	280	—	300	ps
f_{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-17EA	—	500	—	420	—	375	MHz
t_{W_PRI}	Pulse Width for Primary Clock	ECP3-17EA	0. 8	—	0.9	—	1.0	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-17EA	—	310	—	340	—	370	ps
t_{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-17EA	—	220	—	230	—	240	ps
Edge Clock[6]									
f_{MAX_EDGE}	Frequency for Edge Clock	ECP3-150EA	—	500	—	420	—	375	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-150EA	0.9	—	1.0	—	1.2	—	ns
$t_{SKEW\_EDGE\_DQS}$	Edge Clock Skew Within an Edge of the Device	ECP3-150EA	—	200	—	210	—	220	ps
f_{MAX_EDGE}	Frequency for Edge Clock	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-70EA/95EA	0. 9	—	1.0	—	1.2	—	ns
$t_{SKEW\_EDGE\_DQS}$	Edge Clock Skew Within an Edge of the Device	ECP3-70EA/95EA	—	200	—	210	—	220	ps
f_{MAX_EDGE}	Frequency for Edge Clock	ECP3-35EA	—	500	—	420	—	375	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-35EA	0. 9	—	1.0	—	1.2	—	ns
$t_{SKEW\_EDGE\_DQS}$	Edge Clock Skew Within an Edge of the Device	ECP3-35EA	—	200	—	210	—	220	ps
f_{MAX_EDGE}	Frequency for Edge Clock	ECP3-17EA	—	500	—	420	—	375	MHz
t_{W_EDGE}	Clock Pulse Width for Edge Clock	ECP3-17EA	0. 9	—	1.0	—	1.2	—	ns
$t_{SKEW\_EDGE\_DQS}$	Edge Clock Skew Within an Edge of the Device	ECP3-17EA	—	200	—	210	—	220	ps
Generic SDR									
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock Without PLL[2]									
t_{CO}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.9	—	4.3	—	4.7	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
t_H	Clock to Data Hold - PIO Input Register	ECP3-150EA	1.5	—	1.7	—	2.0	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.3	—	1.5	—	1.7	—	ns

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-35EA	683	—	688	—	690	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-35EA	683	—	688	—	690	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-17EA	683	—	688	—	690	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data Aligned at Pin (GDDRX1_TX.SCLK.Aligned)[10]									
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-150EA	—	335	—	338	—	341	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-35EA	—	322	—	320	—	321	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-35EA	—	322	—	320	—	321	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-17EA	—	322	—	320	—	321	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-17EA	—	322	—	320	—	321	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX1_TX.DQS.Centered)[10]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-35EA	670	—	675	—	676	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-35EA	670	—	675	—	676	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-17EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDRX2_TX.Aligned)									
Left and Right Sides									
$t_{DIBGDDR}$	Data Invalid Before Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
$t_{DIAGDDR}$	Data Invalid After Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	500	—	420	—	375	MHz
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Centered at Pin Using DQSDLL (GDDRX2_TX.DQSDLL.Centered)[11]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	All ECP3EA Devices	400	—	400	—	431	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	All ECP3EA Devices	400	—	400	—	432	—	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz

LatticeECP3 Internal Switching Characteristics[1, 2, 5] (Continued)

Over Recommended Commercial Operating Conditions

Parameter	Description	–8		–7		–6		Units.
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.141	—	0.145	—	0.149	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.087	—	0.096	—	0.104	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	–0.066	—	–0.080	—	–0.094	—	ns
t_{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	–0.071	—	–0.070	—	–0.068	—	ns
t_{HBE_EBR}	Byte Enable Hold Time to EBR Output Register	0.118	—	0.098	—	0.077	—	ns
DSP Block Timing[3]								
t_{SUI_DSP}	Input Register Setup Time	0.32	—	0.36	—	0.39	—	ns
t_{HI_DSP}	Input Register Hold Time	–0.17	—	–0.19	—	–0.21	—	ns
t_{SUP_DSP}	Pipeline Register Setup Time	2.23	—	2.30	—	2.37	—	ns
t_{HP_DSP}	Pipeline Register Hold Time	–1.02	—	–1.09	—	–1.15	—	ns
t_{SUO_DSP}	Output Register Setup Time	3.09	—	3.22	—	3.34	—	ns
t_{HO_DSP}	Output Register Hold Time	–1.67	—	–1.76	—	–1.84	—	ns
t_{COI_DSP}	Input Register Clock to Output Time	—	3.05	—	3.35	—	3.73	ns
t_{COP_DSP}	Pipeline Register Clock to Output Time	—	1.30	—	1.47	—	1.64	ns
t_{COO_DSP}	Output Register Clock to Output Time	—	0.58	—	0.60	—	0.62	ns
t_{SUOPT_DSP}	Opcode Register Setup Time	0.31	—	0.35	—	0.39	—	ns
t_{HOPT_DSP}	Opcode Register Hold Time	–0.20	—	–0.24	—	–0.27	—	ns
t_{SUDATA_DSP}	Cascade_data through ALU to Output Register Setup Time	1.69	—	1.94	—	2.14	—	ns
t_{HPDATA_DSP}	Cascade_data through ALU to Output Register Hold Time	–0.58	—	–0.80	—	–0.97	—	ns

1. Internal parameters are characterized but not tested on every device.
2. Commercial timing numbers are shown. Industrial timing numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. DSP slice is configured in Multiply Add/Sub 18 x 18 mode.
4. The output register is in Flip-flop mode.
5. For details on –9 speed grade devices, please contact your Lattice Sales Representative.

LatticeECP3 Family Timing Adders[1, 2, 3, 4, 5, 7] (Continued)

Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
RSDS25	RSDS, VCCIO = 2.5 V	–0.07	–0.04	–0.01	ns
PPLVDS	Point-to-Point LVDS, True LVDS, VCCIO = 2.5 V or 3.3 V	–0.22	–0.19	–0.16	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.67	0.76	0.86	ns
HSTL18_I	HSTL_18 class I 8mA drive, VCCIO = 1.8 V	1.20	1.34	1.47	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.89	1.00	1.11	ns
HSTL18D_I	Differential HSTL 18 class I 8 mA drive	1.20	1.34	1.47	ns
HSTL18D_II	Differential HSTL 18 class II	0.89	1.00	1.11	ns
HSTL15_I	HSTL_15 class I 4 mA drive, VCCIO = 1.5 V	1.67	1.83	1.99	ns
HSTL15D_I	Differential HSTL 15 class I 4 mA drive	1.67	1.83	1.99	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	1.12	1.17	1.21	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	1.08	1.12	1.15	ns
SSTL33D_I	Differential SSTL_3 class I	1.12	1.17	1.21	ns
SSTL33D_II	Differential SSTL_3 class II	1.08	1.12	1.15	ns
SSTL25_I	SSTL_2 class I 8 mA drive, VCCIO = 2.5 V	1.06	1.19	1.31	ns
SSTL25_II	SSTL_2 class II 16 mA drive, VCCIO = 2.5 V	1.04	1.17	1.31	ns
SSTL25D_I	Differential SSTL_2 class I 8 mA drive	1.06	1.19	1.31	ns
SSTL25D_II	Differential SSTL_2 class II 16 mA drive	1.04	1.17	1.31	ns
SSTL18_I	SSTL_1.8 class I, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18_II	SSTL_1.8 class II 8 mA drive, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18D_I	Differential SSTL_1.8 class I	0.70	0.84	0.97	ns
SSTL18D_II	Differential SSTL_1.8 class II 8 mA drive	0.70	0.84	0.97	ns
SSTL15	SSTL_1.5, VCCIO = 1.5 V	1.22	1.35	1.48	ns
SSTL15D	Differential SSTL_15	1.22	1.35	1.48	ns
LVTTL33_4mA	LVTTL 4 mA drive, VCCIO = 3.3V	0.25	0.24	0.23	ns
LVTTL33_8mA	LVTTL 8 mA drive, VCCIO = 3.3V	–0.06	–0.06	–0.07	ns
LVTTL33_12mA	LVTTL 12 mA drive, VCCIO = 3.3V	–0.01	–0.02	–0.02	ns
LVTTL33_16mA	LVTTL 16 mA drive, VCCIO = 3.3V	–0.07	–0.07	–0.08	ns
LVTTL33_20mA	LVTTL 20 mA drive, VCCIO = 3.3V	–0.12	–0.13	–0.14	ns
LVCMOS33_4mA	LVCMOS 3.3 4 mA drive, fast slew rate	0.25	0.24	0.23	ns
LVCMOS33_8mA	LVCMOS 3.3 8 mA drive, fast slew rate	–0.06	–0.06	–0.07	ns
LVCMOS33_12mA	LVCMOS 3.3 12 mA drive, fast slew rate	–0.01	–0.02	–0.02	ns
LVCMOS33_16mA	LVCMOS 3.3 16 mA drive, fast slew rate	–0.07	–0.07	–0.08	ns
LVCMOS33_20mA	LVCMOS 3.3 20 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVCMOS25_4mA	LVCMOS 2.5 4 mA drive, fast slew rate	0.12	0.10	0.09	ns
LVCMOS25_8mA	LVCMOS 2.5 8 mA drive, fast slew rate	–0.05	–0.06	–0.07	ns
LVCMOS25_12mA	LVCMOS 2.5 12 mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVCMOS25_20mA	LVCMOS 2.5 20 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVCMOS18_4mA	LVCMOS 1.8 4 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVCMOS18_8mA	LVCMOS 1.8 8 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVCMOS18_12mA	LVCMOS 1.8 12 mA drive, fast slew rate	–0.04	–0.03	–0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16 mA drive, fast slew rate	–0.04	–0.03	–0.03	ns

SERDES High-Speed Data Transmitter[1]

Table 3-6. Serial Output Timing and Levels

Symbol	Description	Frequency	Min.	Typ.	Max.	Units
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}1.44}$	Differential swing (1.44 V setting)[1, 2]	0.15 to 3.125 Gbps	1150	1440	1730	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}1.35}$	Differential swing (1.35 V setting)[1, 2]	0.15 to 3.125 Gbps	1080	1350	1620	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}1.26}$	Differential swing (1.26 V setting)[1, 2]	0.15 to 3.125 Gbps	1000	1260	1510	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}1.13}$	Differential swing (1.13 V setting)[1, 2]	0.15 to 3.125 Gbps	840	1130	1420	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}1.04}$	Differential swing (1.04 V setting)[1, 2]	0.15 to 3.125 Gbps	780	1040	1300	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}0.92}$	Differential swing (0.92 V setting)[1, 2]	0.15 to 3.125 Gbps	690	920	1150	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}0.87}$	Differential swing (0.87 V setting)[1, 2]	0.15 to 3.125 Gbps	650	870	1090	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}0.78}$	Differential swing (0.78 V setting)[1, 2]	0.15 to 3.125 Gbps	585	780	975	mV, p-p
$V_{TX\text{-}DIFF\text{-}P\text{-}P\text{-}0.64}$	Differential swing (0.64 V setting)[1, 2]	0.15 to 3.125 Gbps	480	640	800	mV, p-p
V_{OCM}	Output common mode voltage	—	V_{CCOB} –0.75	V_{CCOB} –0.60	V_{CCOB} –0.45	V
$T_{TX\text{-}R}$	Rise time (20% to 80%)	—	145	185	265	ps
$T_{TX\text{-}F}$	Fall time (80% to 20%)	—	145	185	265	ps
$Z_{TX\text{-}OI\text{-}SE}$	Output Impedance 50/75/HiZ Ohms (single ended)	—	–20%	50/75/ Hi Z	+20%	Ohms
$R_{LTX\text{-}RL}$	Return loss (with package)	—	10			dB
$T_{TX\text{-}INTRASKEW}$	Lane-to-lane TX skew within a SERDES quad block (intra-quad)	—	—	—	200	ps
$T_{TX\text{-}INTERSKEW}$[3]	Lane-to-lane skew between SERDES quad blocks (inter-quad)	—	—	—	1UI +200	ps

1. All measurements are with 50 Ohm impedance.
2. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for actual binary settings and the min-max range.
3. Inter-quad skew is between all SERDES channels on the device and requires the use of a low skew internal reference clock.

SERDES External Reference Clock

The external reference clock selection and its interface are a critical part of system applications for this product. Table 3-12 specifies reference clock requirements, over the full range of operating conditions.

Table 3-12. External Reference Clock Specification (refclkp/refclkn)

Symbol	Description	Min.	Typ.	Max.	Units
F_{REF}	Frequency range	15	—	320	MHz
$F_{REF-PPM}$	Frequency tolerance[1]	–1000	—	1000	ppm
$V_{REF-IN-SE}$	Input swing, single-ended clock[2]	200	—	V_{CCA}	mV, p-p
$V_{REF-IN-DIFF}$	Input swing, differential clock	200	—	$2*V_{CCA}$	mV, p-p differential
V_{REF-IN}	Input levels	0	—	V_{CCA} + 0.3	V
D_{REF}	Duty cycle[3]	40	—	60	%
T_{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T_{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
$Z_{REF-IN-TERM-DIFF}$	Differential input termination	–20%	100/2K	+20%	Ohms
$C_{REF-IN-CAP}$	Input capacitance	—	—	7	pF

1. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in TN1176, LatticeECP3 SERDES/PCS Usage Guide.
2. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. Lower swings for the clock may be possible, but will tend to increase jitter.
3. Measured at 50% amplitude.

Figure 3-13. SERDES External Reference Clock Waveforms

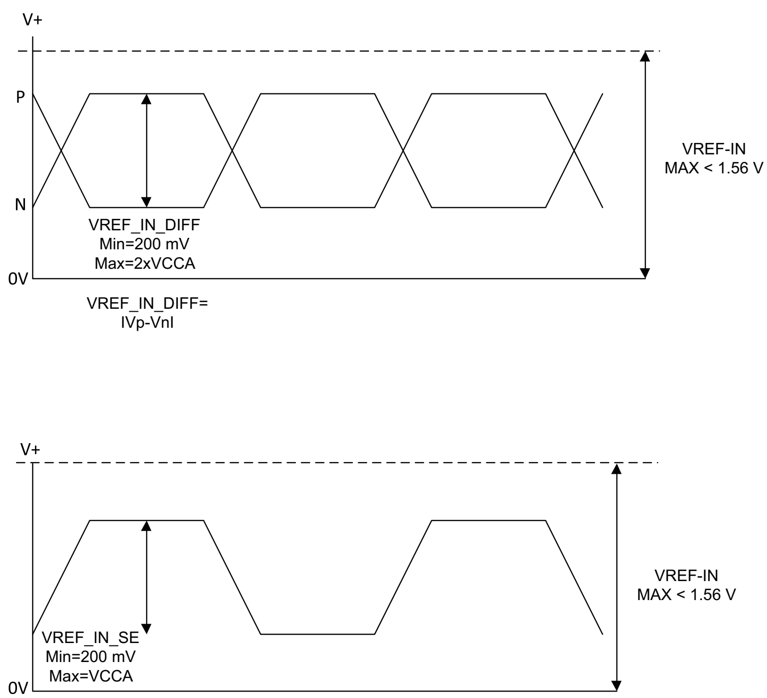


Figure 3-16. Jitter Transfer – 1.25 Gbps

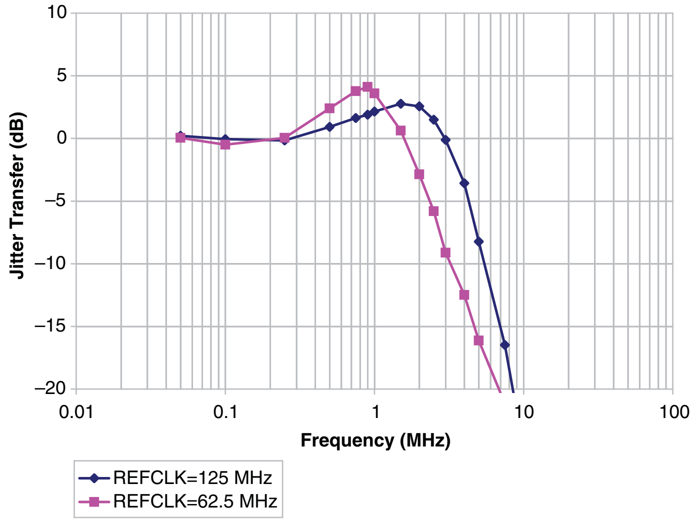
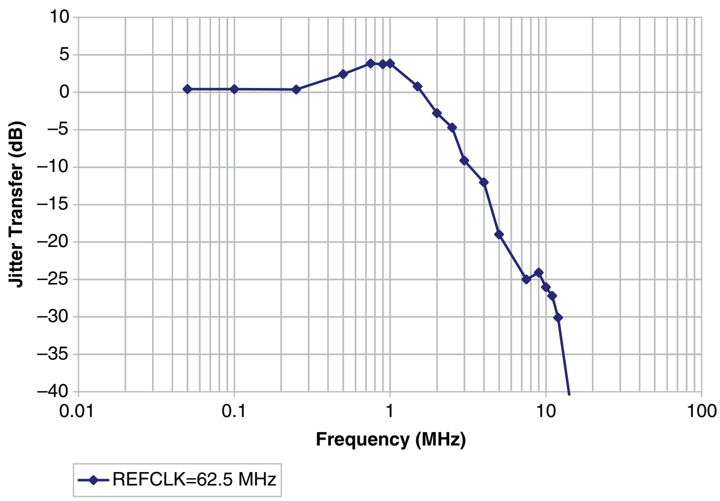


Figure 3-17. Jitter Transfer – 622 Mbps



XAUI/Serial Rapid I/O Type 3/CPRI LV E.30 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-13. Transmit

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[2, 3, 4]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ}[1, 2, 3, 4]	Total output data jitter		—	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Values are measured at 2.5 Gbps.

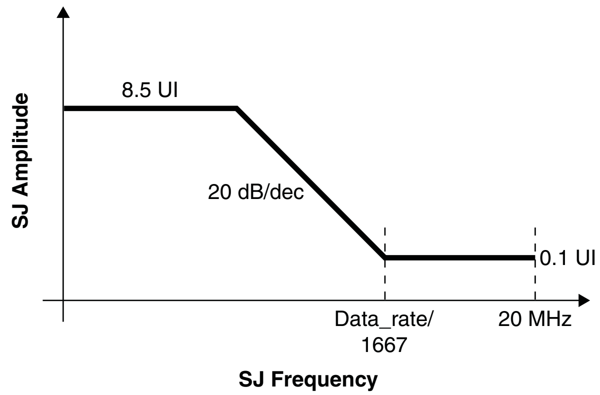
Table 3-14. Receive and Jitter Tolerance

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[1, 2, 3]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ}[1, 2, 3]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ}[1, 2, 3]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ}[1, 2, 3]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

Figure 3-18. XAUI Sinusoidal Jitter Tolerance Mask



Note: The sinusoidal jitter tolerance is measured with at least 0.37 UIpp of Deterministic jitter (Dj) and the sum of Dj and Rj (random jitter) is at least 0.55 UIpp. Therefore, the sum of Dj, Rj and Sj (sinusoidal jitter) is at least 0.65 UIpp (Dj = 0.37, Rj = 0.18, Sj = 0.1).

HDMI (High-Definition Multimedia Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-22. Transmit and Receive[1, 2]

Symbol	Description	Spec. Compliance		Units
		Min. Spec.	Max. Spec.	
Transmit				
Intra-pair Skew		—	75	ps
Inter-pair Skew		—	800	ps
TMDS Differential Clock Jitter		—	0.25	UI
Receive				
R_T	Termination Resistance	40	60	Ohms
V_{ICM}	Input AC Common Mode Voltage (50-Ohm Setting)	—	50	mV
TMDS Clock Jitter	Clock Jitter Tolerance	—	0.25	UI

1. Output buffers must drive a translation device. Max. speed is 2 Gbps. If translation device does not modify rise/fall time, the maximum speed is 1.5 Gbps.
2. Input buffers must be AC coupled in order to support the 3.3 V common mode. Generally, HDMI inputs are terminated by an external cable equalizer before data/clock is forwarded to the LatticeECP3 device.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672I	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672I	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672I	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6LFN672I	1.2 V	–6	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7LFN672I	1.2 V	–7	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8LFN672I	1.2 V	–8	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156I	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156I	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156I	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-6LFN1156I	1.2 V	–6	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7LFN1156I	1.2 V	–7	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8LFN1156I	1.2 V	–8	LOW	Lead-Free fpBGA	1156	IND	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149

1. Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.
   - The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
   - The SERDES XRES pin on the TW device passes CDM testing at 250V.

Date	Version	Section	Change Summary
			Updated Simplified Channel Block Diagram for SERDES/PCS Block diagram.
			Updated Device Configuration text section.
			Corrected software default value of MCCLK to be 2.5 MHz.
		DC and Switching Characteristics	Updated VCCOB Min/Max data in Recommended Operating Conditions table.
			Corrected footnote 2 in sysIO Recommended Operating Conditions table.
			Added added footnote 7 for t_{SKEW_PRIB} to External Switching Characteristics table.
			Added 2-to-1 Gearing text section and table.
			Updated External Reference Clock Specification (refclkp/refclkn) table.
			LatticeECP3 sysCONFIG Port Timing Specifications - updated t_{DINIT} information.
			Added sysCONFIG Port Timing waveform.
			Serial Input Data Specifications table, delete Typ data for $V_{RX\text{-}DIFF\text{-}S}$.
			Added footnote 4 to sysCLOCK PLL Timing table for t_{PFD}.
			Added SERDES/PCS Block Latency Breakdown table.
			External Reference Clock Specifications table, added footnote 4, add symbol name vREF-IN-DIFF.
			Added SERDES External Reference Clock Waveforms.
			Updated Serial Output Timing and Levels table.
			Pin-to-pin performance table, changed "typically 3% slower" to "typically slower".
			Updated timing information
			Updated SERDES minimum frequency.
			Added data to the following tables: External Switching Characteristics, Internal Switching Characteristics, Family Timing Adders, Maximum I/O Buffer Speed, DLL Timing, High Speed Data Transmitter, Channel Output Jitter, Typical Building Block Function Performance, Register-to-Register Performance, and Power Supply Requirements.
			Updated Serial Input Data Specifications table.
			Updated Transmit table, Serial Rapid I/O Type 2 Electrical and Timing Characteristics section.
		Pinout Information	Updated Signal Description tables.
			Updated Pin Information Summary tables and added footnote 1.
February 2009	01.0	—	Initial release.